

S4D02120F

1200V SIC POWER SCHOTTKY RECTIFIERS



Description

This 1200V 2A diode is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D02120F is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C TJ operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	1200	V
Average Rectified Forward Current	$I_F (AV)1$	$T_c=25^{\circ}C$	8	A
	$I_F (AV)2$	$T_c=147^{\circ}C$	2	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM1}	10ms, Half Sine pulse, $T_c=25^{\circ}C$	27	A
	I_{FSM2}	10ms, Half Sine pulse, $T_c=110^{\circ}C$	25	A
Repetitive Peak Forward Surge Current	I_{FRM1}	10ms, Half Sine pulse, $T_c=25^{\circ}C$	16	A
	I_{FRM2}	10ms, Half Sine pulse, $T_c=110^{\circ}C$	14	A
Non-Repetitive Peak Forward Surge Current	$I_{F,Max1}$	10 μ s. Pulse, $T_c=25^{\circ}C$	200	A
	$I_{F,Max2}$	10 μ s. Pulse, $T_c=110^{\circ}C$	160	A
Power Dissipation	P_{tot1}	$T_c=25^{\circ}C$	37	W
	P_{tot2}	$T_c=110^{\circ}C$	16	W

Electrical Characteristics:

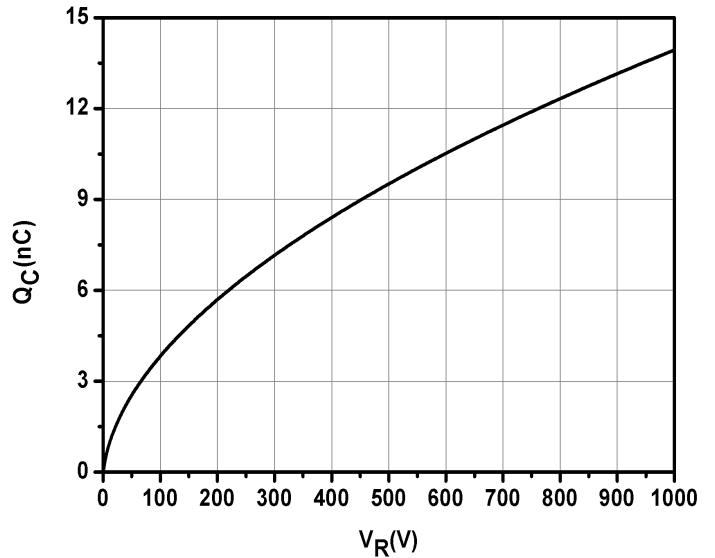
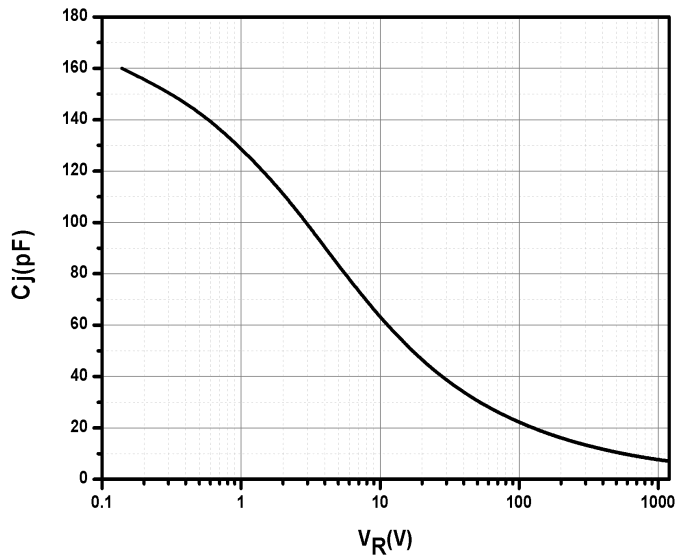
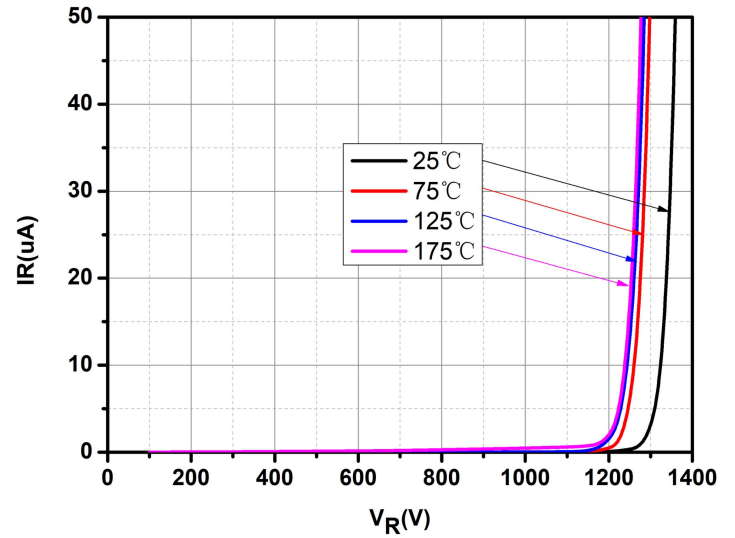
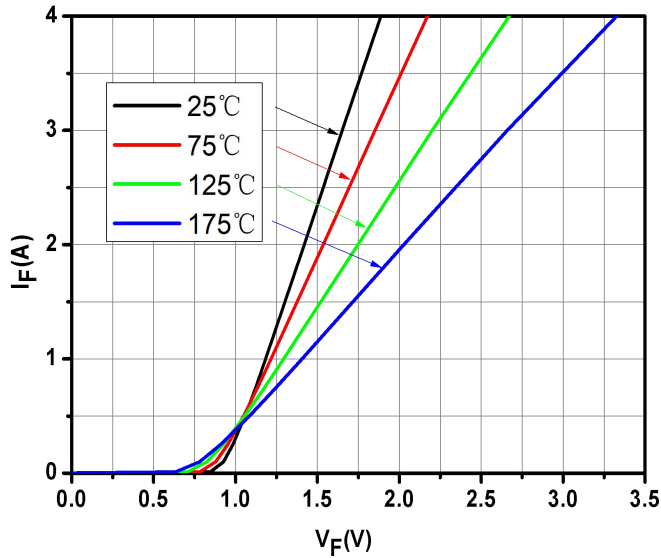
Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 2A, Pulse, $T_J = 25^{\circ}C$	1.4	1.8	V
	V_{F2}	@ 2A, Pulse, $T_J = 175^{\circ}C$	2.0	2.5	V
Reverse Current*	I_{R1}	@ V_R = rated V_R $T_J = 25^{\circ}C$	1	10	μ A
	I_{R2}	@ V_R = rated V_R $T_J = 175^{\circ}C$	2	40	μ A
Junction Capacitance	C_T	$V_R=0V$, $T_J=25^{\circ}C$, $f=1MHz$	160	-	pF
Reverse Recovery Charge	Q_c	$I_F = 2A$, $di/dt = 200A/\mu s$ $V_R = 800V$, $T_J = 25^{\circ}C$	12.33	-	nC
Capacitance Stored Energy	E_C	$V_R = 800V$, $T_J = 25^{\circ}C$	6.33	-	μ J

* Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	$^{\circ}C$
Storage Temperature	T_{stg}	-	-55 to +175	$^{\circ}C$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	4	$^{\circ}C/W$

Ratings and Characteristics Curves



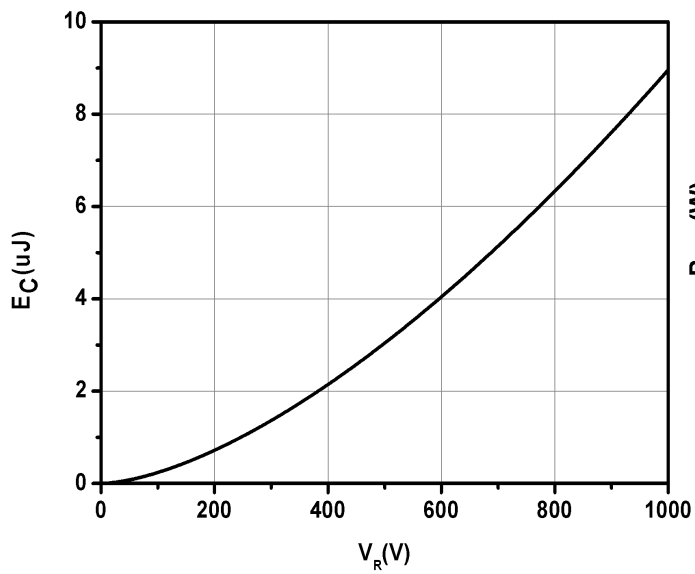


Fig.5-Capacitance Stored Energy

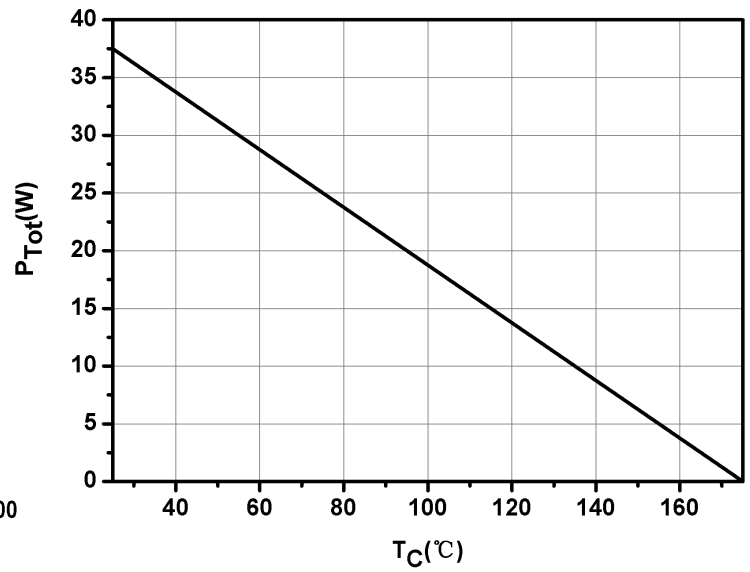


Fig.6-Power Derating

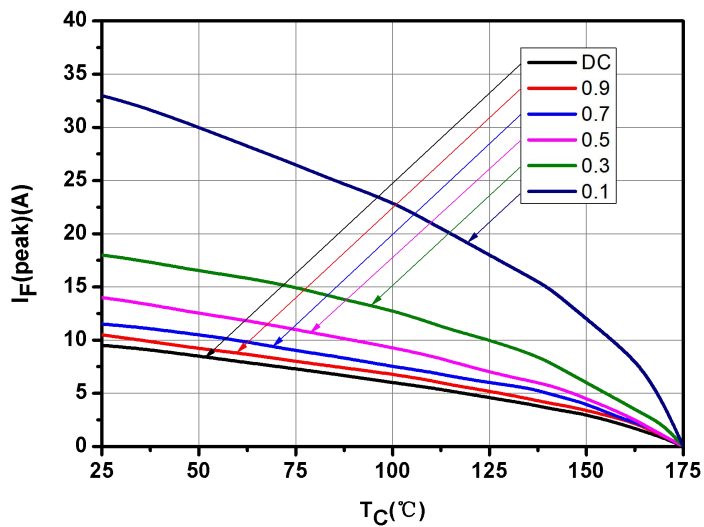
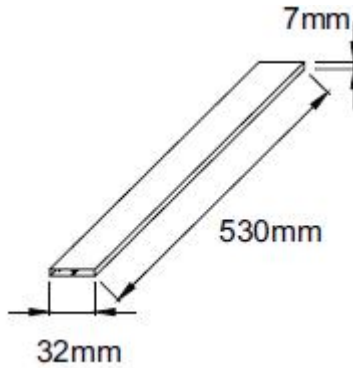


Fig.7-Current Derating

Ordering Information

Device	Package	Shipping
S4D02120F	ITO-220AC(TO-220MF-2L)	50pcs / tube

Tube Specification



Marking Diagram

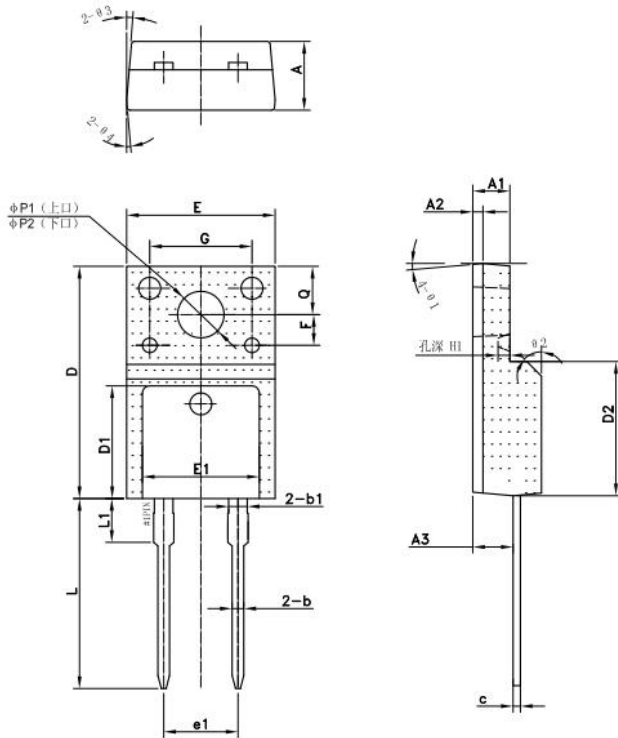


Where XXXXX is YYWWL

S4D = Device Type
F = Package type
02 = Forward Current (2A)
120 = Reverse Voltage (1200V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL : 94V-0

Mechanical Dimensions



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2		0.70	
A3	2.56	2.76	2.96
b	0.70	0.80	0.95
b1		1.28	
c	0.45	0.50	0.65
D	15.67	15.87	16.07
D1		7.70	
D2		9.12	
E	9.96	10.16	10.36
E1		8.00	
e1		5.08	
F		2.1	
G		7	
H1		0.81	
L	12.48	12.98	13.20
L1		2.93	
φP1 (上口)	2.98	3.18	3.38
φP2 (下口)	3.20	3.40	3.60
Q	3.10	3.30	3.50
θ1		5°	
θ2		45°	
θ3		5°	
θ4		5°	

Technical Data
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